



LHCb Silicon Detectors: Operational Experience and Run I \rightarrow Run II Transition

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Experiment dedicated to the studies of rare heavy quark decays and \mathcal{CP} violation



Single-arm forward spectrometer $(2 < \eta < 5)$

Tracking System RICH Calorimetry Muon system





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Vertex Locator (VELO): Detector

- 21 module in each half
- First active strip at $r \approx 8 \text{ mm}$
- Sensors retractable for injection
- Sensors kept in a secondary beam vacuum separated by an undulated aluminum foil
- \blacktriangleright ~ 172k readout channels







Vertex Locator (VELO): Sensor

- Two single-sided silicon micro strip sensors (n⁺-on-n by Micron; n⁺-on-p in the most upstream module)
 - r-sensors: four 45° quadrants
 - Φ-sensors: two regions (inner and outer)
- Thickness: 300 μm;
 Strip pitch: 38-102 μm
- Double metal layer for signal routing
- Sensors at $\sim -10^{\circ}\,C$
- ▶ 99.6 % of channels working







The Tracker Turicensis (TT)

- Silicon micro strip sensors (p⁺-on-n by Hamamatsu Photonics K.K.)
- Thickness: 500 μm; Strip pitch: 183 μm
- Readout strips length up to 37 cm ⇒ up to 60 pF
- \blacktriangleright ~ 144k readout channels
- Total area: 8 m²
- Sensors at \sim 8° C
- 99.7 % of channels working (averaged over Run I)









The Inner Tracker (IT)

- Silicon micro strip sensors (p⁺-on-n by Hamamatsu Photonics K.K.)
- Twelve layers
- Thickness: 320 (1 sensor, 11 cm) or 410 μm (2 sensors, 22 cm); Strip pitch: 198 μm
- $\blacktriangleright~\sim$ 130k read out channels
- Total area: 4.2 m²
- ► Sensors at ~ 8° C
- 98.6% of channels working (averaged over Run I)









Signal-to-Noise Ratio (VELO)

[JINST 9 (2014) P09007]

Measured with 1-strip clusters assigned to VELO tracks Ratio of most probable ADC value to 1-strip common-mode subtracted noise



Impact of routing lines on 1-strip common-mode subtracted noise





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Signal-to-Noise Ratio (TT + IT)

Measured with clusters assigned to tracks with $p > 5 \,\text{GeV/c}$ Ratio of most probable ADC value to 1-strip common-mode subtracted noise







Hit Resolution (VELO)

[JINST 9 (2014) P09007]

Hit resolution dependent on strip pitch and projected angle

Unbiased track residuals used to determine the resolution



Hit resolution of 4 μ m achieved for small pitch and optimal angle





[JINST 9 (2014) P090071

Spatial Alignment (VELO): Sensors

Optical and mechanical measurements before installation

- Software alignment based on
 - the Millipede method [NIM A596 (2008), 157]
 - the residuals of a Kalman filter fit [NIM A600 (2009), 471]
- \Rightarrow alignment precision for sensors better than 4 μm







Spatial Alignment (VELO): Halves

[JINST 9 (2014) P09007]

Centering of the VELO required due to the closing of the VELO at the beginning of each fill

Based on the *x*- and *y*measurement of the reconstructed primary vertices in each half

Fully automated and done within 210 s after stable beams

 \Rightarrow stability of the alignment within 5 μm









Spatial Alignment (TT + IT)

Tracking stations are aligned by minimising all track residuals from a Kalman filter fit [NIM **A600** (2009), 471]

Mass constraints $(J/\psi(1S) \rightarrow \mu^+\mu^- \text{ and } D^0 \rightarrow K^{\pm}\pi^{\mp})$ used to suppress weak modes.

[NIM A712 (2013), 48]

TT hit resolution (incl. alignment): 53.4 μm (Binary resolution: 53 μm) IT hit resolution (incl. alignment): 54.9 μm (Binary resolution: 57 μm)







Running Conditions



Delivered integrated luminosity: 2010: 0.04 fb⁻¹ 2011: 1.22 fb⁻¹ 2012: 2.21 fb⁻¹

Integrated luminosity in 2010-2012: 3.5 fb⁻¹

Designed lifetime of TT and IT: 10 years with 2 fb^{-1} /year Designed lifetime of VELO: 5 years with 2 fb^{-1} /year





Running Conditions

FLUKA simulation tuned to dose measurements in the cavern:



Maximal 1 MeV neutron equivalent flux:

$$\begin{array}{lll} \mbox{VELO} & \mbox{TT} & \mbox{IT} \\ 8.0 \times 10^7 \, \mbox{cm}^{-2} \mbox{s}^{-1} & \mbox{1.0} \times 10^6 \, \mbox{cm}^{-2} \mbox{s}^{-1} & \mbox{9.2} \times 10^4 \, \mbox{cm}^{-2} \mbox{s}^{-1} \end{array}$$





Radiation Damage Monitoring

Leakage Currents:

Change in the band structure of the silicon (bulk current)

Depletion Voltage:

Change in the effective doping concentration induced by irradiation





Radiation Damage Monitoring

Leakage Currents:

Change in the band structure of the silicon (bulk current)

 $I_{\text{leak}} = \alpha \cdot \Phi \cdot V$

Temperature dependence of the bulk current:

$$\frac{I_{\text{leak}}(T_1)}{I_{\text{leak}}(T_2)} = \left(\frac{T_1}{T_2}\right)^2 \cdot \exp\left(-\frac{E_g}{2k_B}\left(\frac{1}{T_1} - \frac{1}{T_2}\right)\right)$$
$$E_g: \text{ band gap of silicon}$$
$$T_{1,2}: \text{ temperatures}$$





Leakage Currents (VELO)

[JINST 8 (2013) P08002]



Measurements normalised to $-7^{\circ}C$ Prediction based on mean 1-MeV-n equivalent fluence

 \Rightarrow Good agreement between measurements and predictions





Leakage Currents (VELO): Temperature scans

Temperature scans allow to measure contributions from surface and bulk currents



Expected exponential variation of bulk currents

Surface currents in the VELO behave ohmically and anneal with particle fluence September 15, 2014 LHCb Silicon Detectors - Christian Elsasser





Leakage Currents (TT + IT)



Data normalised to a temperature of 8° C ($E_g = 1.21$ eV)





Leakage Currents (TT + IT)



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Depletion Voltage

Charge Collection Efficiency (CCE) scans:

Dedicated runs (3-4 times per year) with scanning of bias voltage in VELO/tracking stations







Depletion Voltage

Charge Collection Efficiency (CCE) scans:



Extraction of effective depletion voltage by fraction of plateau ADC counts \Rightarrow calibrated with depletion voltage measurements after production and early CCE scans





[JINST 8 (2013) P08002]

Depletion Voltage (VELO)

Initial EDV: Type: Effective Depletion Voltage [V n-on-p n-on-n n-on-n n-on-n Hamburg model 20 10 LHCb VELO 1012 25 30 35 n 5 10 15 20 40 1 MeV n_{eq} fluence

- ▶ Type inversion of sensors at $\Phi_{1-MeV-n eq} = (1.0 1.5) \times 10^{13} \text{ cm}^{-2}$
- ► Good agreement with the Hamburg model [NIM A426 (1999) 87]
- Sensors can be operated up to 500 V.





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Depletion Voltage (TT): Pulse Shape

Thicker sensor \Rightarrow larger ballistic deficit

High bias voltage (400 V):

Low bias voltage (60 V):



Timing scan performed in each voltage step

Extraction of Charge Equivalent as integral of the pulse shape





Depletion Voltage (TT)



- No type inversion so far
- Good agreement with the Hamburg model (also for considering annealing and reverse annealing terms for single sensor)

► Sensors can be operated up to 500 V.





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Work during LS1

Detectors perform very well

- \Rightarrow No major intervention on all three sub-detectors
 - Replacement of the TT/IT chiller and maintenance of the cooling system
 - Maintenance of the VELO vacuum system
 - Scheduled maintenance of HV/LV supplies
 - Minor repair work on the electronics (DAQ, Slow control)
 - ► Restructuring of ECS software (*e.g.* transition from PVSS to WinCC)
 - Installation of alignment monitor system in IT based on two BCAMs (Brandeis CCD Angle Monitor) per station





50 ns \rightarrow 25 ns Transition

Aim for 25 ns bunch spacing \Rightarrow Higher spill-over hit rate

Possible modifications:

- Modification of sampling time and signal shaping
- Usage of "spill-over" bit to identify tracks reconstructed from spill-over hits







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Summary & Conclusion

- Excellent performance of LHCb's silicon detectors during Run I
 - excellent hit resolution
 - measured signal-to-noise ratios close to expectations
 - contributing to very precise impact parameter
 - ... and invariant mass measurements
- Radiation damage monitored via leakage currents and Charge Collection Efficiency scans also in good agreement with predictions
- ► No significant degradation of the physics performance observed
- Standard maintenance work performed during LS1
- ► Possible changes in the operation due to 25 ns bunch spacing
- VELO, TT and IT are looking forward to LHC Run II





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Backup







Material Budget (VELO)

High vertex resolution \Rightarrow less multiple scattering \Rightarrow small amount of material between the interaction point and the first measurement



Dominated by the 300 μm thin aluminum foil separating the primary and the secondary beam vacuum





Material Budget (VELO)







TT Module







Detector Readout







Hit Efficiency (IT)

Analysis of tracks from $D^0 \rightarrow K^+ K^-$ decays (p > 10 GeV/c) Extrapolate each track to the sensors and search hit within a certain window Average hit efficiency $\varepsilon > 99 \%$







Cluster Size (VELO)

Dominating cluster size (1-, 2-, 3- or 4-strip cluster) dependent on projected angle and strip pitch







Cluster Finding Efficiency (VELO)

Cluster Finding Efficiency decreases with increasing irradiation and bias voltage

- 100 Possible explaination based on charge collection by the routing lines on the 2nd metal layer



90

Efficiency depends on distance to nearest strip and nearest routing line No measurable effect on the tracking





Time Alignment (TT + IT)

Synchronis ation of trigger and control signals in the entire LHCb detector necessary (time of flight, cable length)

Samples spaced by 25 ns with internal shift of sampling point by -6, 0, +6, +12 ns

Extract most probable value from distribution of ADC counts and fit pulse shape

Timing alignment of TT and IT with collision data better than 1 ns







Broken Bond Problem (TT)

- Breaking of bonds between pitch adapter and readout chip
- Only inner most row affected











High Voltage Problem (TT)



- Abnormally high currents (far above 10 μA)
- Correlation with instantaneous luminosity
- Sectors which are closest to the wall of the detector box are affected

 \Rightarrow Installation of Kapton shielding on the detector box walls and bias voltage kept on in between fills





High Voltage Problem (TT)

No High Currents after installation of the Kapton shielding:









Residual background from missed extrapolation or ghost tracks

Photon conversion taken into account







Timing scan performed in each voltage step

Extraction of Charge Equivalent as integral of the pulse shape





July 2011: January 2013: Charge Equivalent [ADC value] Charge Equivalent [ADC value] 400 500 V_{bias} [V] 400 500 V_{bias} [V]

Depletion voltage V_{depl} extracted from a third-order spline as the voltage where the fit function reaches about 95% of its maximal value (calibration with measurements from the first CCE scan and V_{depl} measured after production)







Also good agreement between V_{depl} values measured from CCE scans and estimated from the Hamburg model and running conditions in less irradiated sensors.





Change in the depletion voltage:

July 2011:

January 2013:



Average fluence for the six innermost sensors is not equal.





Model Parameters for Leakage Currents

Parameter	Value
α_0	(6.67±0.09)×10 ^{−17} A/cm
α_1	(7.23±0.06)×10 ^{−17} A/cm
k ₀	$(4.2 \pm 0.5) imes 10^{13} ext{ s}^{-1}$
E _a	(1.11±0.05) eV





Model Parameters for Depletion Voltage

Parameter	Value
$N_{C0} \cdot c$	$(7.5 \pm 0.6) \times 10^{-2} \text{ cm}^{-1}$
g _c	$(1.60\pm0.04) imes10^{-2}~{ m cm^{-1}}$
g_a	$(1.40\pm0.14) imes10^{-2} \ { m cm^{-1}}$
g_Y	$(5.70\pm0.09) imes10^{-2} \ { m cm^{-1}}$
<i>k</i> _{0,<i>a</i>}	$(2.4 \pm 1.0) \times 10^{13} \text{ s}^{-1}$
<i>k</i> _{0,<i>Y</i>}	$(1.5 \pm 1.1) \times 10^{15} \text{ s}^{-1}$
E _{aa}	(1.09±0.03) eV
E _Y	(1.31±0.03) eV





Impact Parameter and Decay Time Resolution



- Impact parameter and decay time resolution are important feature for B physics (identification of b hadrons and oscillation/CP measurements)
- ► Impact parameter resolution of about 25 μ m for a track with $p_{\rm T} = 2 \ {\rm GeV}/c$
- Primary vertex resolution of about 13 μm (x/y) and 80 μm (z) (vertex with 25 tracks)





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Invariant Mass Resolution

Very good mass resolution an essential ingredient for precision measurements and high signal-to-background ratio

LHCb performed the most precise mass measurements for several *B* hadrons.



Most precise mass resolution among the LHC experiments for particles with masses below the Z mass $J/\psi \rightarrow \mu^+\mu^-$: 12 MeV/ c^2 , $D^0 \rightarrow K^-\pi^+$: 7.5 MeV/ c^2